

General Description:

The LWD3003AD3 uses trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications. The package form is PDFN3.3*3.3-8L, which accords with the ROHS standard and Halogen Free standard.

Features:

- Fast Switching
- Low Gate Charge and $R_{DS(ON)}$
- Low Reverse transfer capacitances

Applications:

- DC-DC Converter
- Portable Equipment
- Power Management

100% DVDS Tested

100% Avalanche Tested



Package Marking and Ordering Information:

Marking	Part Number	Package	Packing	Qty.
D3003A/LW D3/D.C.	LWD3003AD3	PDFN3.3*3.3-8L	Reel	5000 Pcs

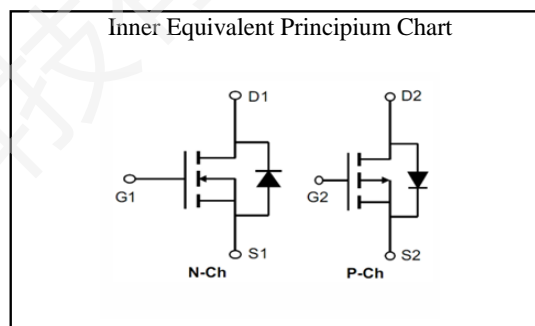
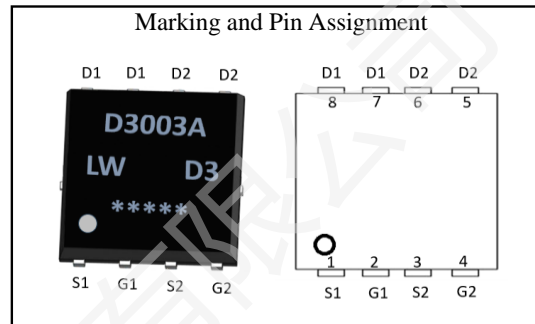
Absolute Maximum Ratings:

Symbol	Parameter	Value		Units	
		N-Ch	P-Ch		
V_{DSS}	Drain-to-Source Voltage	30	-30	V	
I_D	Continuous Drain Current	$T_C=25^\circ\text{C}$	23	-16	A
	Continuous Drain Current	$T_C=100^\circ\text{C}$	15	-10.2	A
I_{DM}^{a1}	Pulsed Drain Current		92	-64	A
E_{AS}^{a2}	Single pulse avalanche energy		20	20	mJ
V_{GS}	Gate-to-Source Voltage		± 20	± 20	V
P_D	Power Dissipation		14	14	W
T_J, T_{STG}	Operating Junction and Storage Temperature Range		150, -55 to 150		$^\circ\text{C}$
T_L	Maximum Temperature for Soldering		260		$^\circ\text{C}$

Thermal Characteristics:

Symbol	Parameter	Value		Units
		N-Ch	P-Ch	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	8.9	8.9	$^\circ\text{C}/\text{W}$
$R_{\theta JA}^{a3}$	Thermal Resistance, Junction-to-Ambient	45	45	$^\circ\text{C}/\text{W}$

Symbol	N-Ch	P-Ch	Units
V_{DSS}	30	-30	V
I_D	23	-16	A
$R_{DS(ON) \text{ TYPE}}$	11	24	$\text{m}\Omega$



N-Channel Electrical Characteristic ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise specified):

Static Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
V_{DSS}	Drain to Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	30	--	--	V
I_{DSS}	Drain to Source Leakage Current	$V_{DS}=30V, V_{GS}=0V$	--	--	1.0	μA
$I_{GSS(F)}$	Gate to Source Forward Leakage	$V_{GS}=+20V, V_{DS}=0V$	--	--	100	nA
$I_{GSS(R)}$	Gate to Source Reverse Leakage	$V_{GS}=-20V, V_{DS}=0V$	--	--	-100	nA
$V_{GS(TH)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	1.0	1.5	2.0	V
$R_{DS(ON)1}$	Drain-to-Source On-Resistance	$V_{GS}=10V, I_D=15A$	--	11	14	$m\Omega$
$R_{DS(ON)2}$	Drain-to-Source On-Resistance	$V_{GS}=4.5V, I_D=10A$	--	15	25	$m\Omega$

Dynamic Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
C_{iss}	Input Capacitance	$V_{GS}=0V$	--	637	--	pF
C_{oss}	Output Capacitance	$V_{DS}=15V$	--	98	--	
C_{riss}	Reverse Transfer Capacitance	$f=1.0MHz$	--	85	--	
R_G	Gate resistance	$V_{GS}=0V, V_{DS}=0V, f=1MHz$	--	1.9	--	Ω

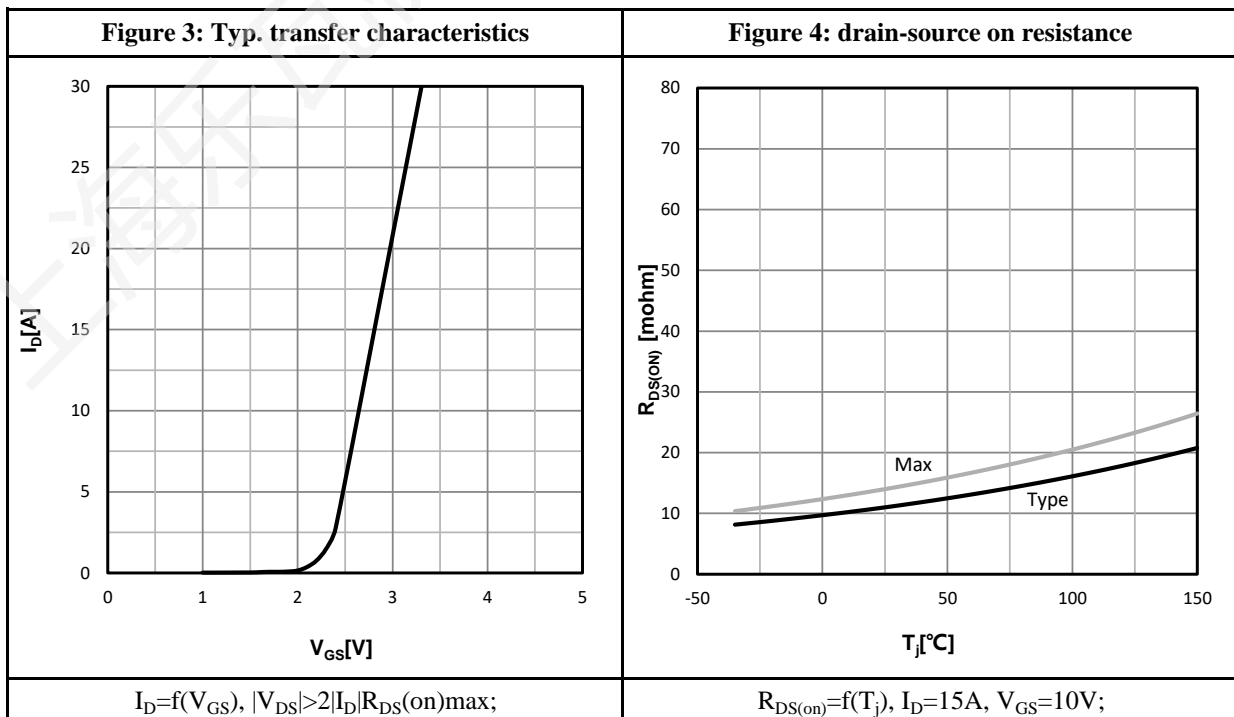
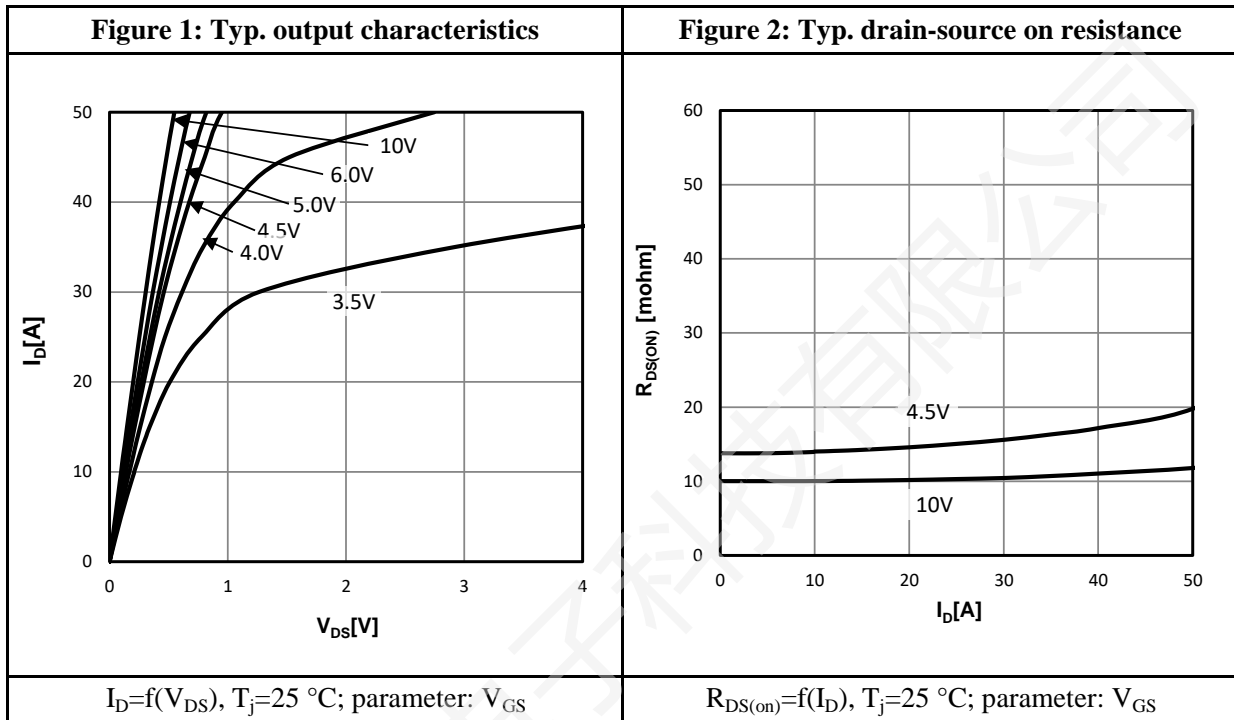
Resistive Switching Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
$t_{d(ON)}$	Turn-on Delay Time	$I_D=15A$	--	5.0	--	ns
t_r	Rise Time	$V_{DS}=15V$	--	2.0	--	
$t_{d(OFF)}$	Turn-Off Delay Time	$V_{GS}=10V$	--	13	--	
t_f	Fall Time	$R_G=6.0\Omega$	--	3.0	--	
Q_g	Total Gate Charge	$V_{GS}=10V$	--	15	--	nC
Q_{gs}	Gate to Source Charge	$V_{DS}=15V$	--	2.0	--	
Q_{gd}	Gate to Drain Charge	$I_D=15A$	--	2.9	--	

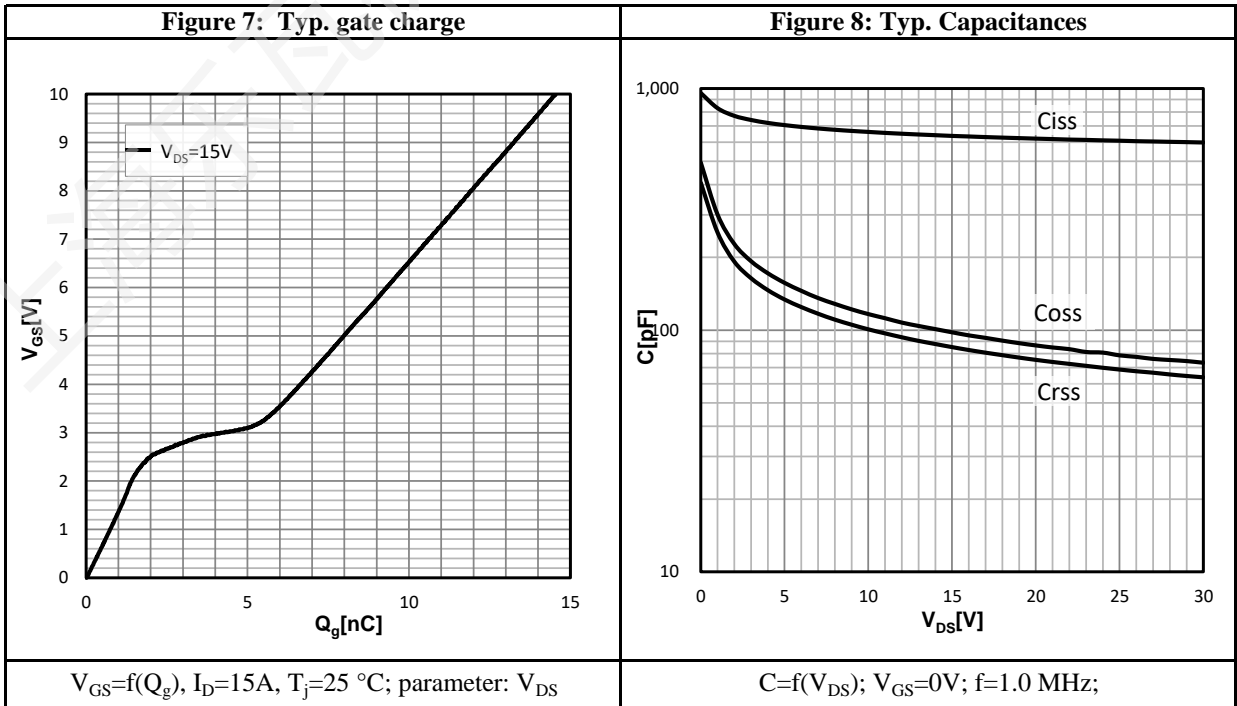
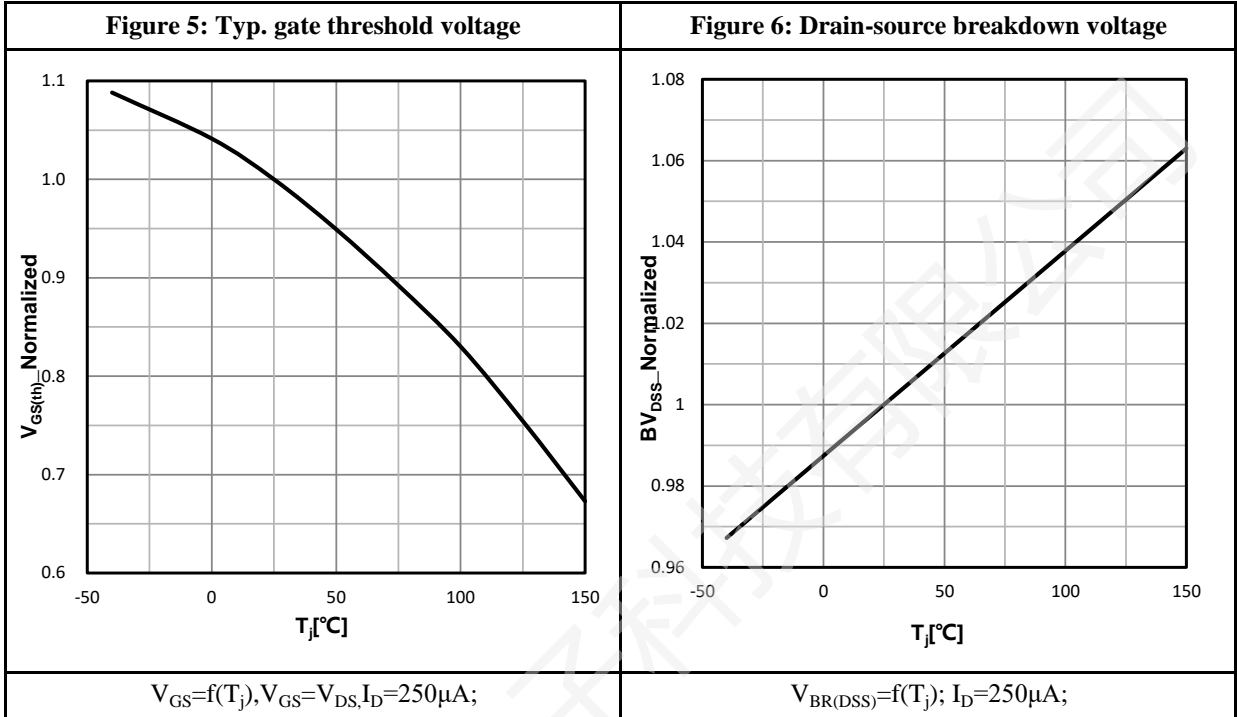
Source-Drain Diode Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
I_S	Diode Forward Current	$T_C=25\text{ }^\circ\text{C}$	--	--	23	A
V_{SD}	Diode Forward Voltage	$I_S=15A, V_{GS}=0V$	--	--	1.2	V

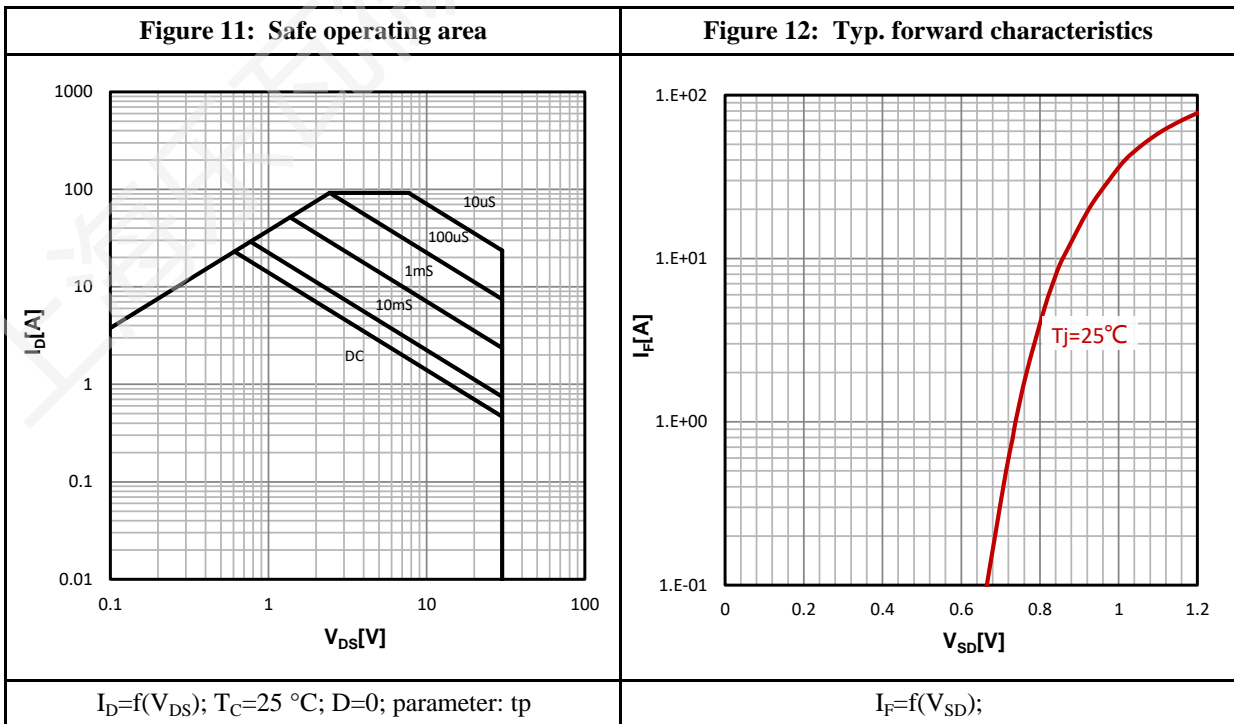
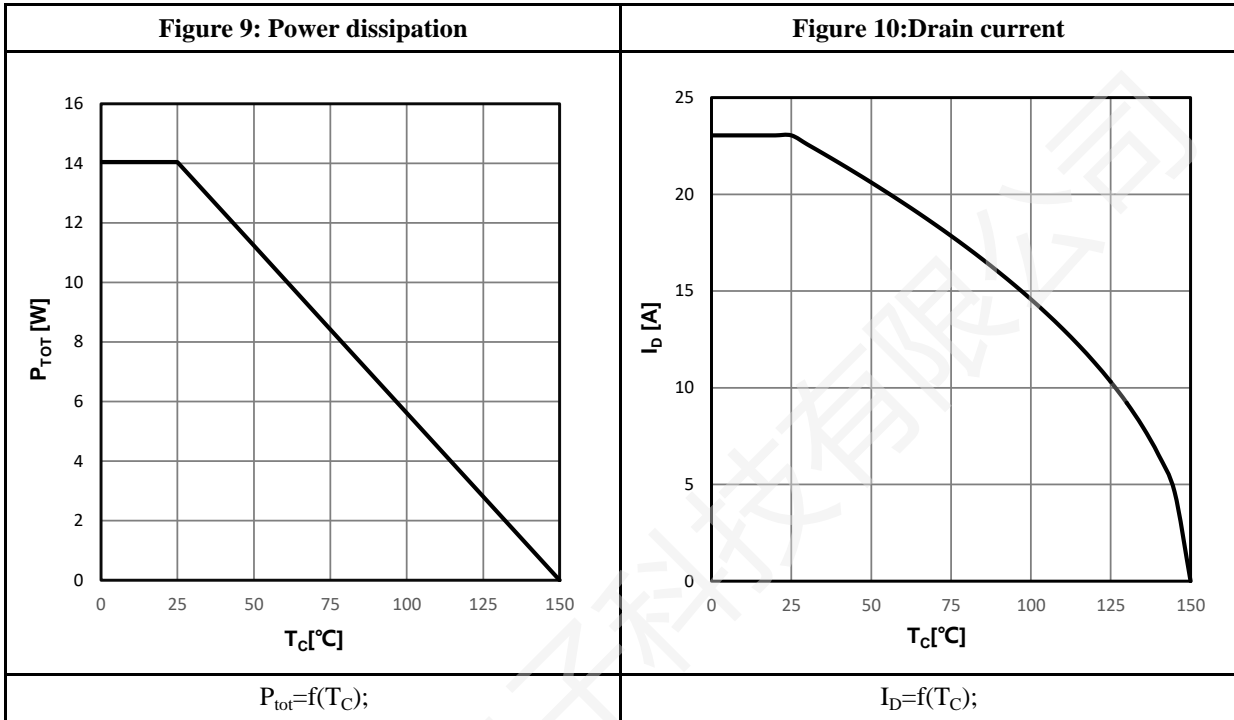
a1: Repetitive rating; pulse width limited by maximum junction temperature

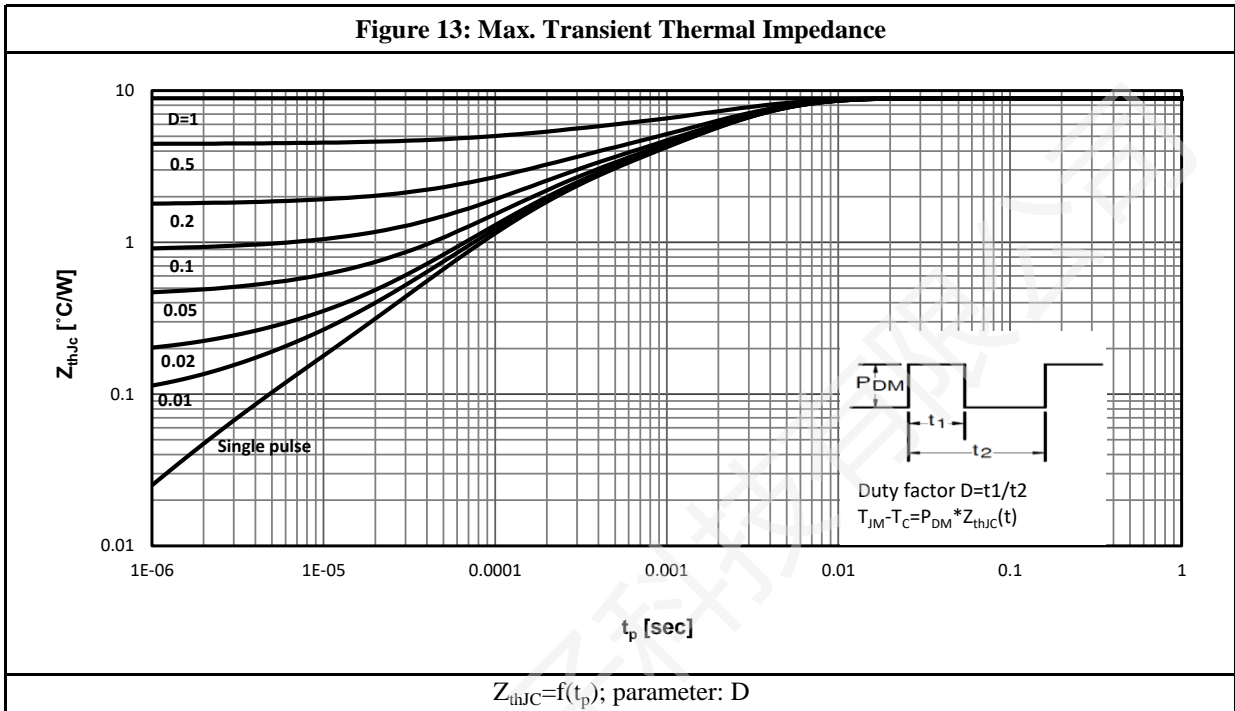
a2: $V_{DD}=15V, L=0.1mH, R_G=25\Omega$, Starting $T_J=25\text{ }^\circ\text{C}$

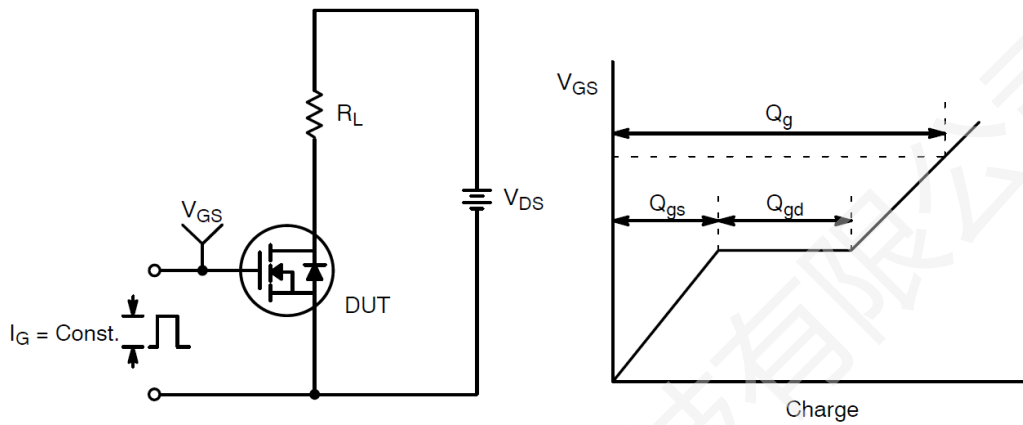
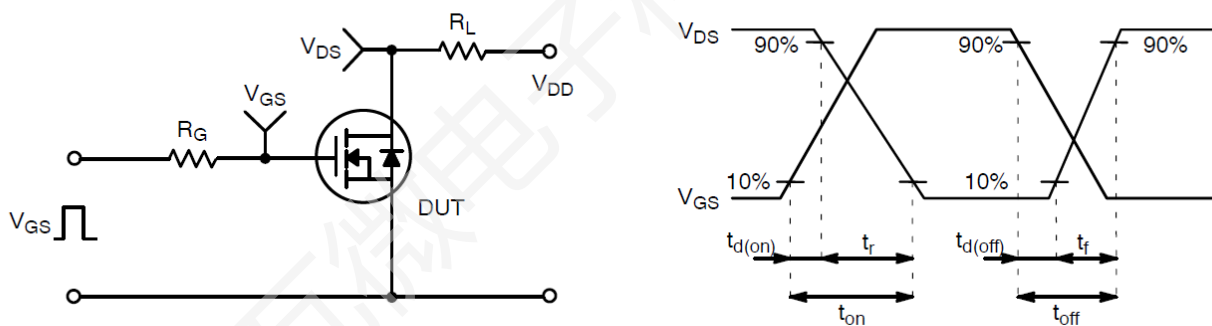
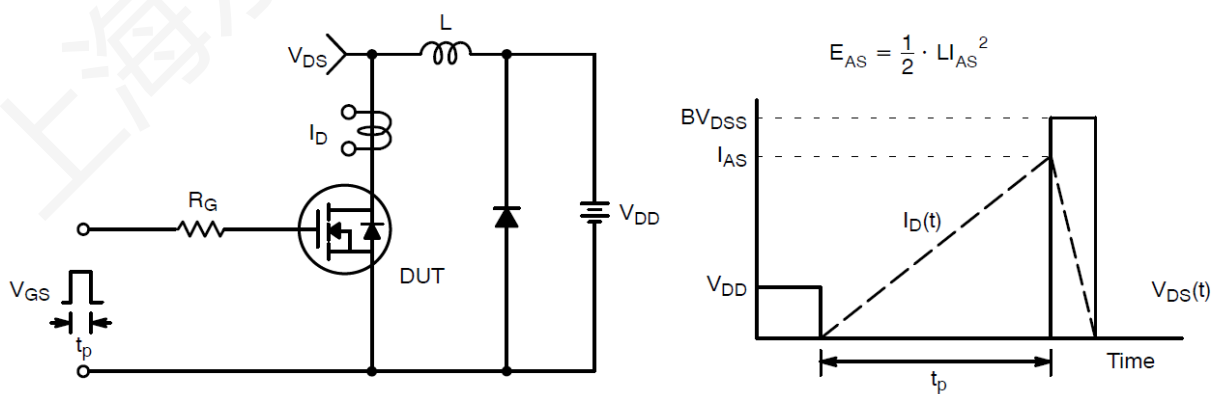
a3: Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 μm thick) copper area for drain connection.

N-Channel Characteristics Curve:








Test Circuit & Waveform:

Figure 14: Gate Charge Test Circuit & Waveform

Figure 15: Resistive Switching Test Circuit & Waveforms

Figure 16: Unclamped Inductive Switching Test Circuit & Waveforms

P-Channel Electrical Characteristic ($T_j = 25\text{ }^\circ\text{C}$, unless otherwise specified):

Static Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
V_{DSS}	Drain to Source Breakdown Voltage	$V_{GS}=0V, I_D=-250\mu A$	-30	--	--	V
I_{DSS}	Drain to Source Leakage Current	$V_{DS}=-30V, V_{GS}=0V$	--	--	-1.0	μA
$I_{GSS(F)}$	Gate to Source Forward Leakage	$V_{GS}=-20V, V_{DS}=0V$	--	--	-100	nA
$I_{GSS(R)}$	Gate to Source Reverse Leakage	$V_{GS}=+20V, V_{DS}=0V$	--	--	100	nA
$V_{GS(TH)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=-250\mu A$	-1.1	-1.6	-2.1	V
$R_{DS(ON)1}$	Drain-to-Source On-Resistance	$V_{GS}=-10V, I_D=-10A$	--	24	31	$m\Omega$
$R_{DS(ON)2}$	Drain-to-Source On-Resistance	$V_{GS}=-4.5V, I_D=-8.0A$	--	34	47	$m\Omega$

Dynamic Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
C_{iss}	Input Capacitance	$V_{GS}=0V$	--	685	--	pF
C_{oss}	Output Capacitance	$V_{DS}=-15V$	--	97	--	
C_{rss}	Reverse Transfer Capacitance	$f=1.0MHz$	--	88	--	
R_G	Gate resistance	$V_{GS}=0V, V_{DS}=0V, f=1MHz$	--	11	--	Ω

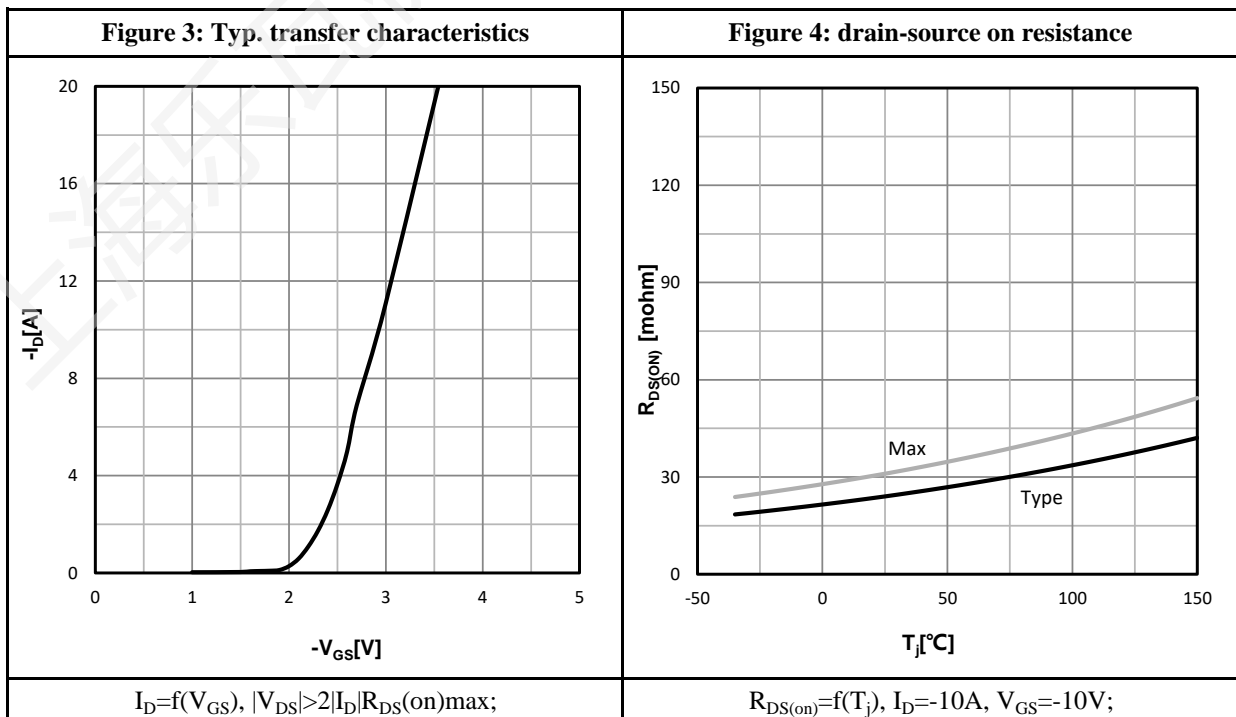
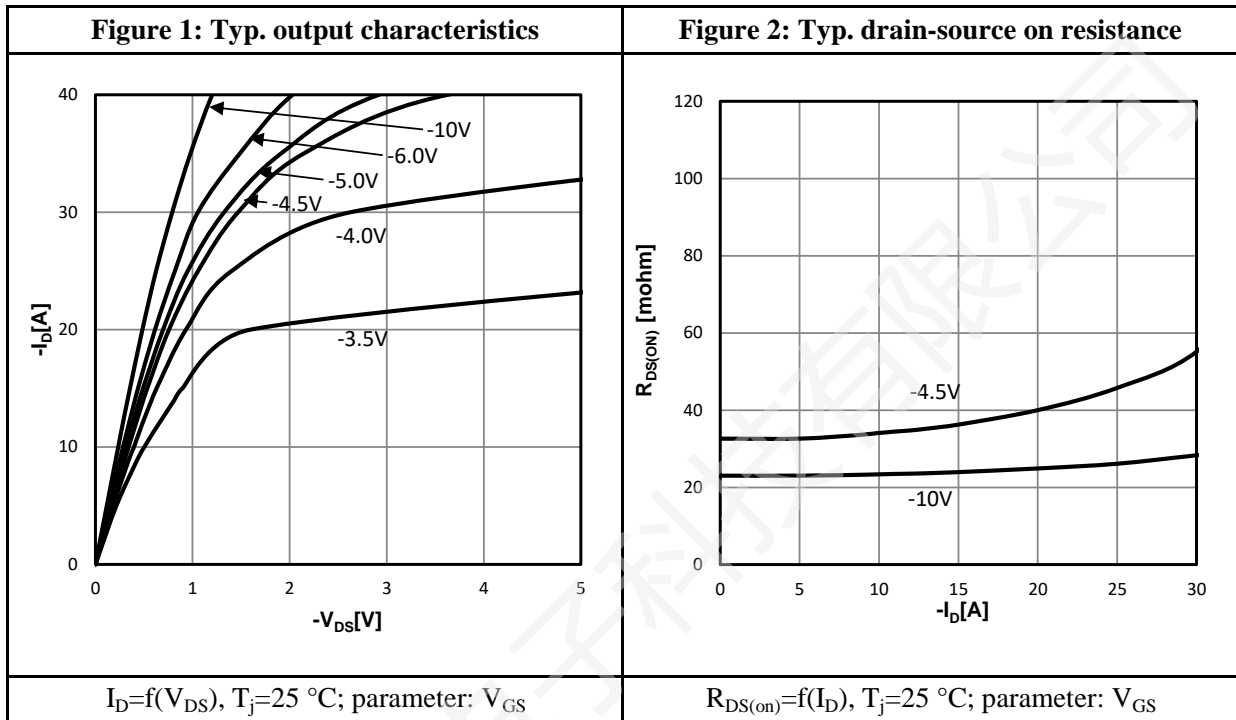
Resistive Switching Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
$t_{d(ON)}$	Turn-on Delay Time	$I_D=-10A$	--	7.0	--	ns
t_r	Rise Time	$V_{DS}=-15V$	--	6.0	--	
$t_{d(OFF)}$	Turn-Off Delay Time	$V_{GS}=-10V$	--	17	--	
t_f	Fall Time	$R_G=3.0\Omega$	--	5.0	--	
Q_g	Total Gate Charge	$V_{GS}=-10V$	--	16	--	nC
Q_{gs}	Gate to Source Charge	$V_{DS}=-15V$	--	2.0	--	
Q_{gd}	Gate to Drain Charge	$I_D=-8.0A$	--	3.0	--	

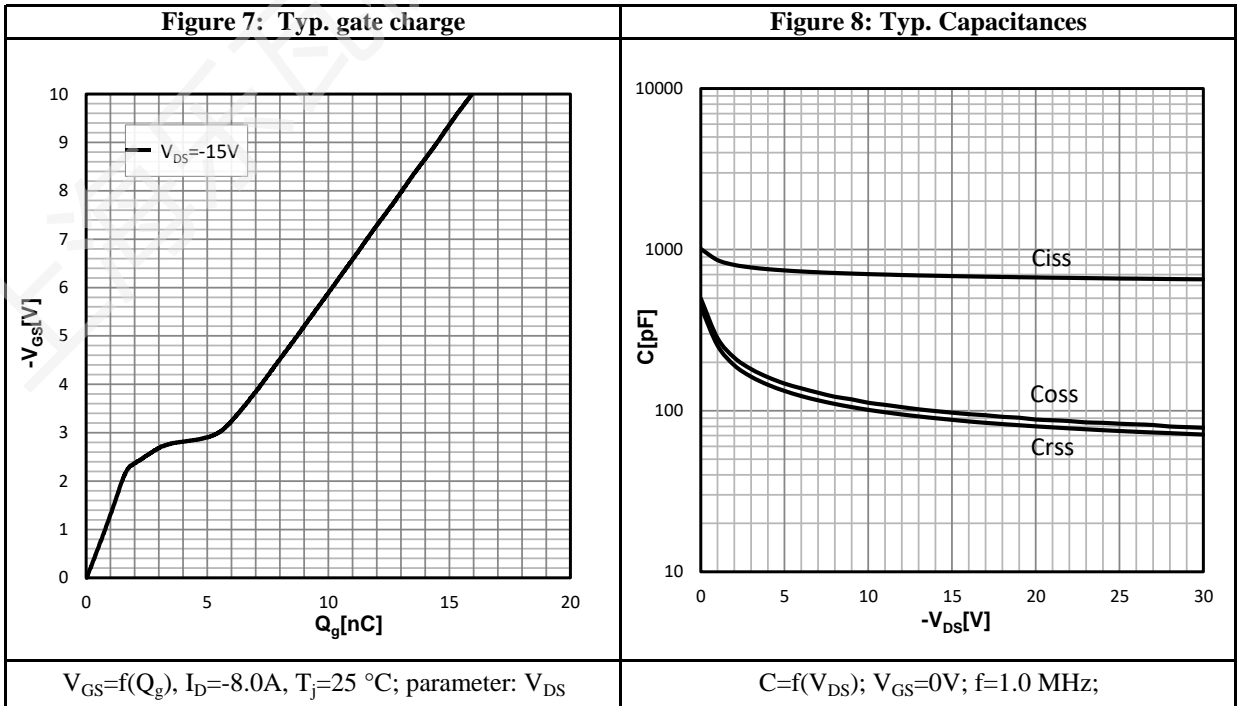
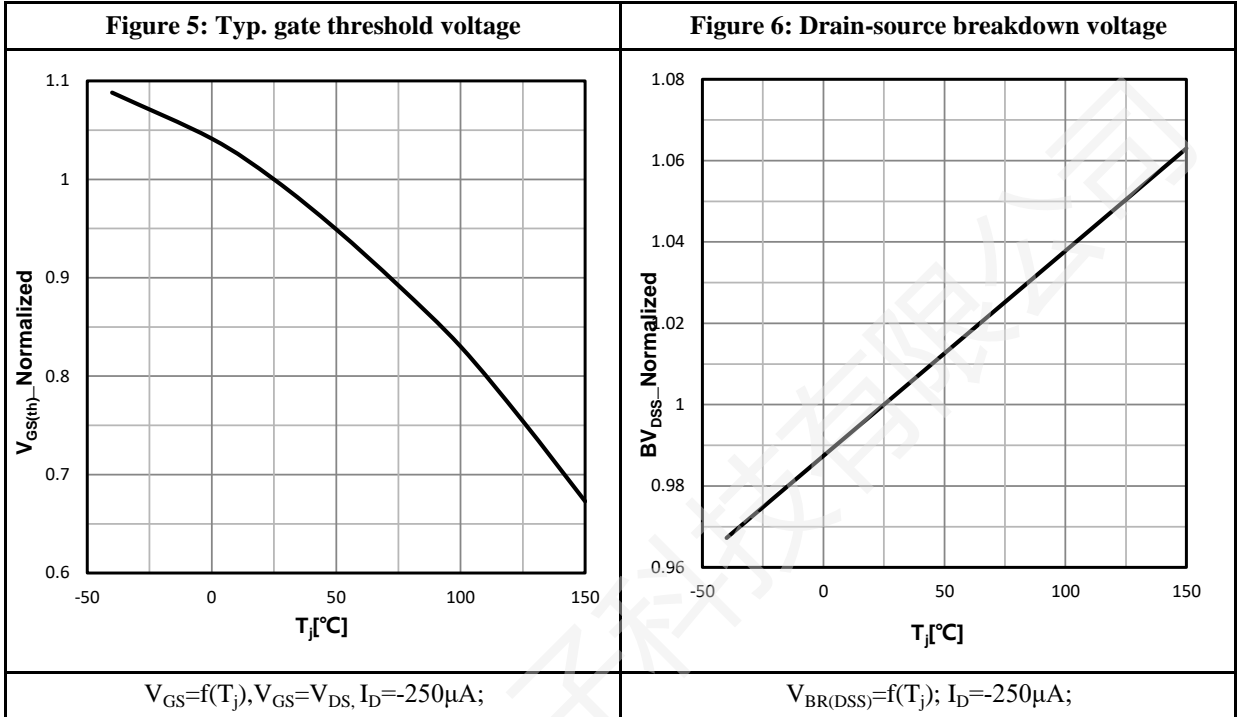
Source-Drain Diode Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
I_S	Diode Forward Current	$T_C=25\text{ }^\circ\text{C}$	--	--	-16	A
V_{SD}	Diode Forward Voltage	$I_S=-10A, V_{GS}=0V$	--	--	-1.2	V

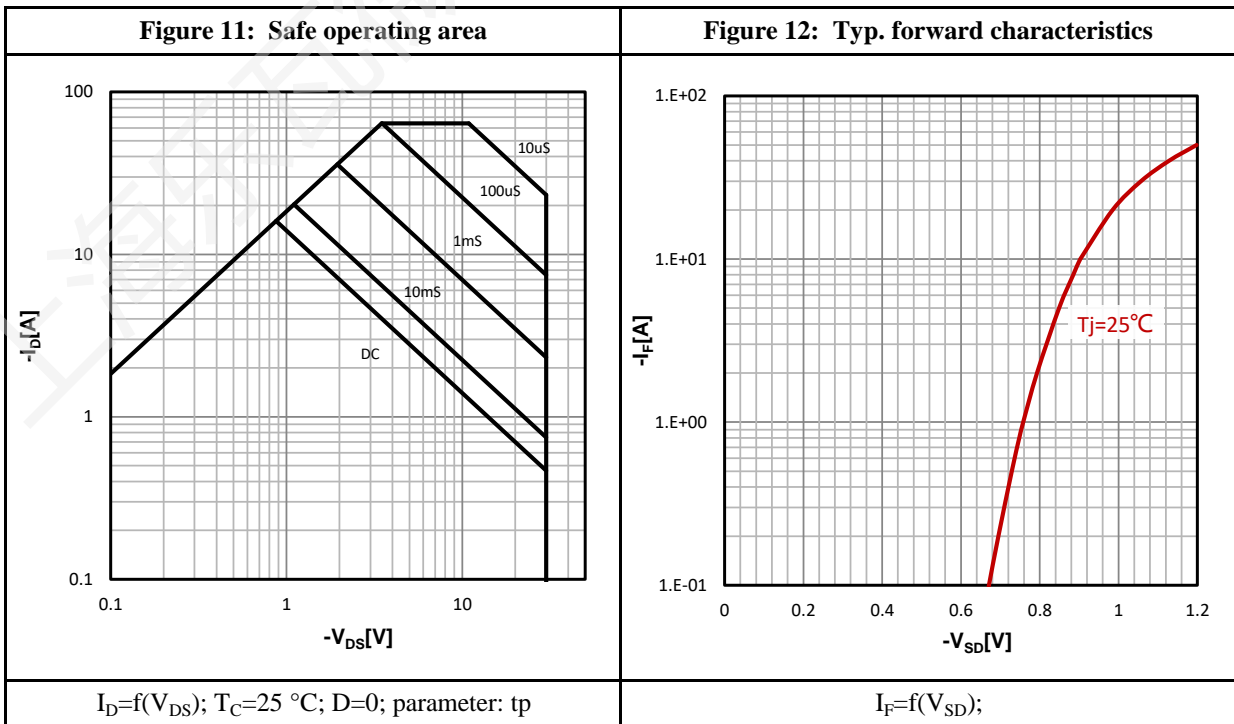
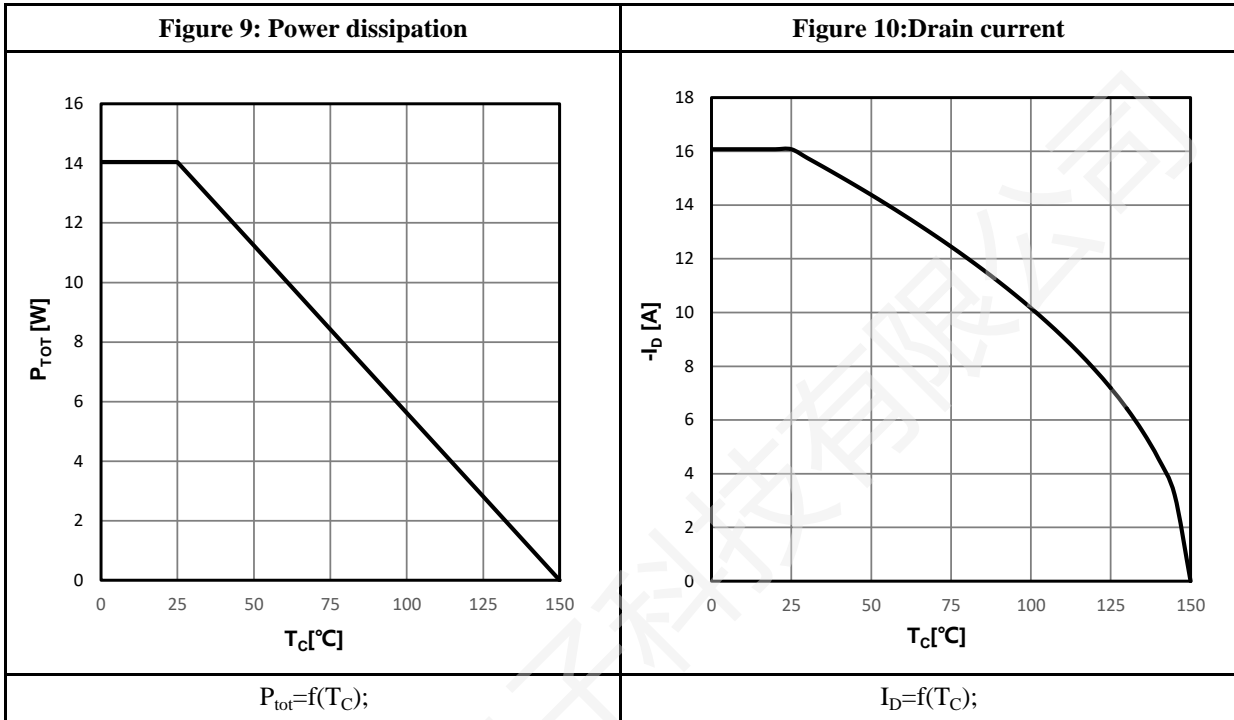
a1: Repetitive rating; pulse width limited by maximum junction temperature

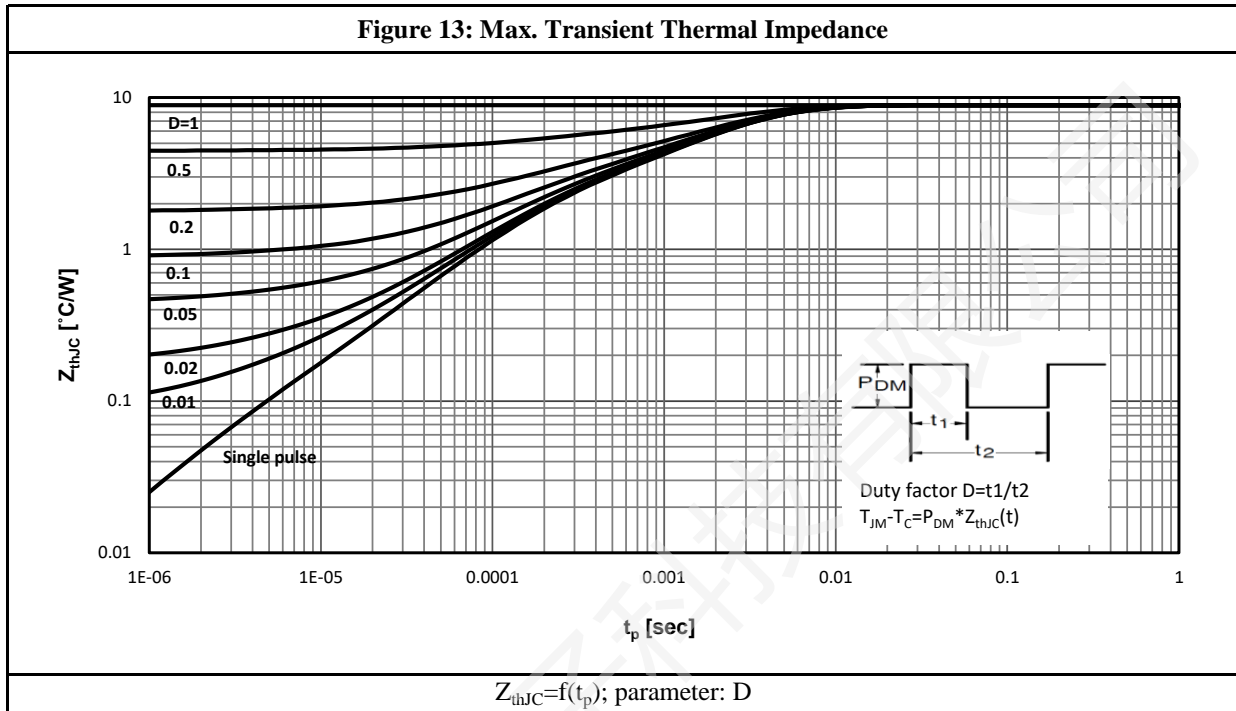
a2: $V_{DD}=-15V, L=0.1mH, R_G=25\Omega$, Starting $T_j=25\text{ }^\circ\text{C}$

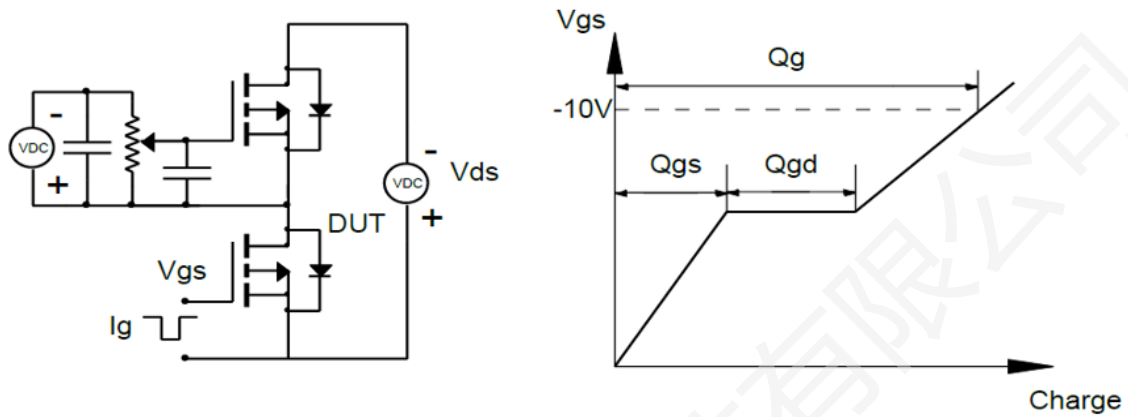
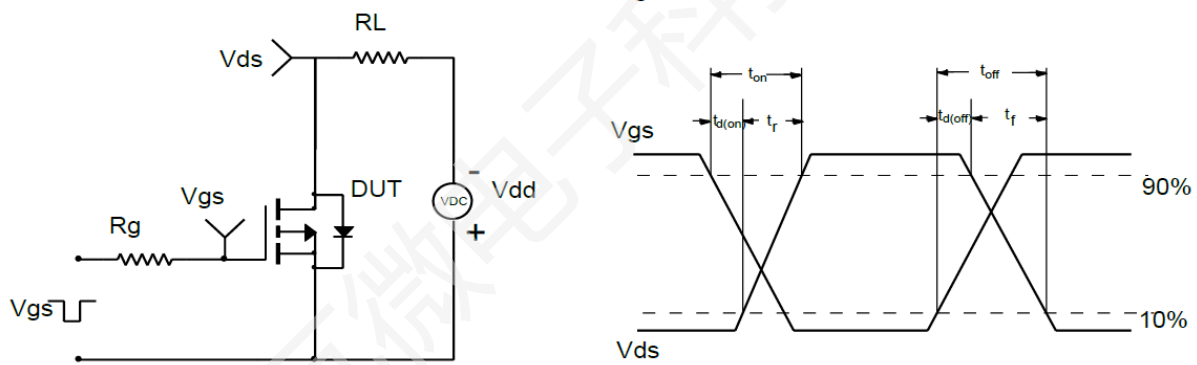
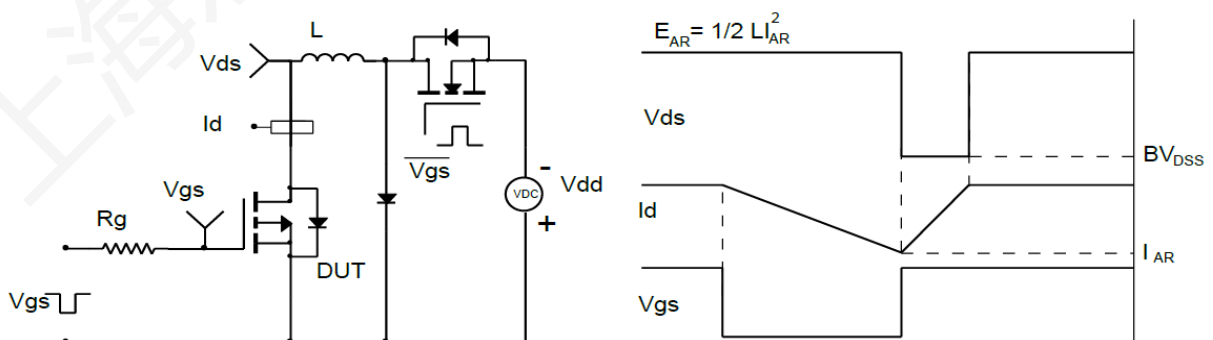
a3: Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 μm thick) copper area for drain connection.

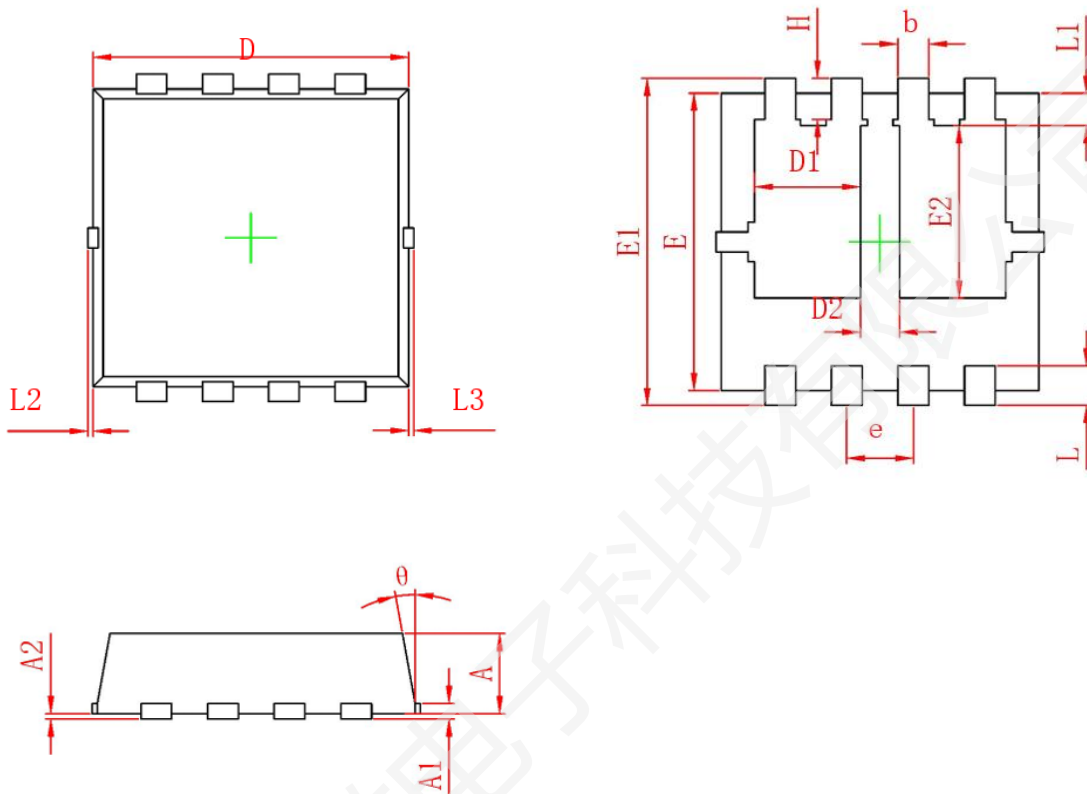
P-Channel Characteristics Curve:








P-Channel Test Circuit & Waveform:

Figure 14: Gate Charge Test Circuit & Waveform

Figure 15: Resistive Switching Test Circuit & Waveforms

Figure 16: Unclamped Inductive Switching Test Circuit & Waveforms

Package Outline:


Symbol	MILLIMETER	
	MIN	MIN
A	0.700	0.900
A1	0.152 REF	
A2	0~0.05	
D	3.000	3.200
D1	0.935	1.135
D2	0.280	0.480
E	2.900	3.100
E1	3.150	3.450
E2	1.535	1.935
b	0.200	0.400
e	0.550	0.750
L	0.300	0.500
L1	0.180	0.480
L2	0~0.100	
L3	0~0.100	
H	0.315	0.515
θ	8°	12°

Revision History:

Revison	Date	Descriptions
Rev 1.0	Jun.2025	Initial Version

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Mailing Address: Unit 02&04&05, 10th Floor, Building 5, No.666 Shengxia Road, No.122 Yindong Road,
China (Shanghai) Pilot Free Trade Zone
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